Leiditech

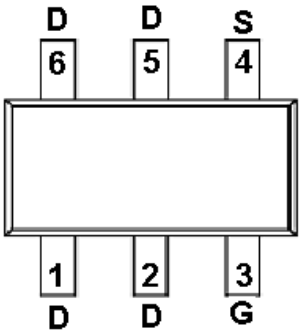
LM6L3N10

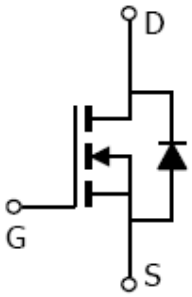
100V N-Channel Enhancement Mode MOSFET

DESCRIPTION

The LM6L3N10 is the N-Channel logic enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. The LM6L3N10 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

PIN CONFIGURATION(SOT-23-6L)





FEATURES

- 100V/3A,$R_{DS(ON)}$= 310mΩ@V_{GS}= 10V
- High density cell design for extremely low RDS (ON)
- Exceptional on-resistance and maximum DC current capability
- SOT-23-6L package design

APPLICATIONS

- Powered System
- DC/DC Converter
- Load Switch

Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LM6L3N10	WAN	SOT-23-6L	-	-	3000 units

ABSOULTE MAXIMUM RATINGS (T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	3.0	A
	T_A=70℃		2.0	
Pulsed Drain Current		I_{DM}	10	A
Power Dissipation	T_A=25℃	P_D	1.25	W
	T_A=70℃		0.8	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

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ELECTRICAL CHARACTERISTICS (T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1	2.0	2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V			1	uA
		V_{DS}=80V,V_{GS}=0V T_J=125℃			5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≥5V,V_{GS} =10V	3.0			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}= 10V,I_D=3A		0.26	0.31	Ω
Forward Transconductance	gfs	V_{DS}=10V,I_D=3A		2.4		S
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS} =0V			1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=80V,V_{GS}=10V I_D= 5A		9	13	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	V_{DS}=25,V_{GS}=0V f=1MHz		508		pF
Output Capacitance	C_{oss}			29		
Reverse Transfer Capacitance	C_{rss}			16.5		
Turn-On Time	$t_{d(on)}$	V_{DD}=50V,R_L=10Ω I_D=3A,V_{GEN}=10V R_G=3.3Ω		2		nS
	t_r			21.5		
Turn-Off Time	$t_{d(off)}$			11.2		
	t_f			18.8		

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Typical Performance Characteristics

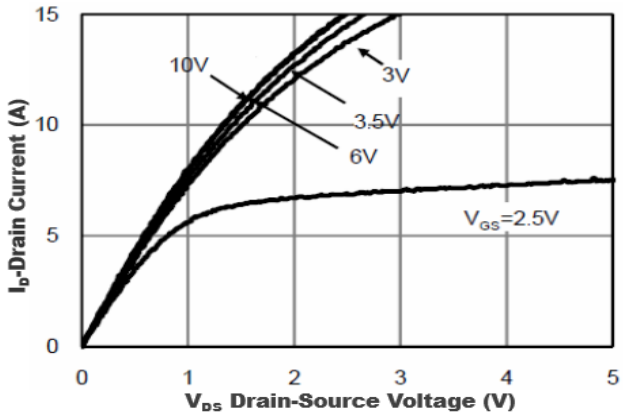


Figure1. Output Characteristics

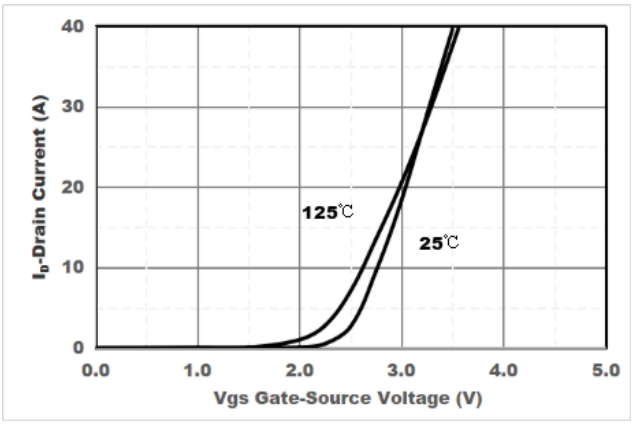


Figure2. Transfer Characteristics

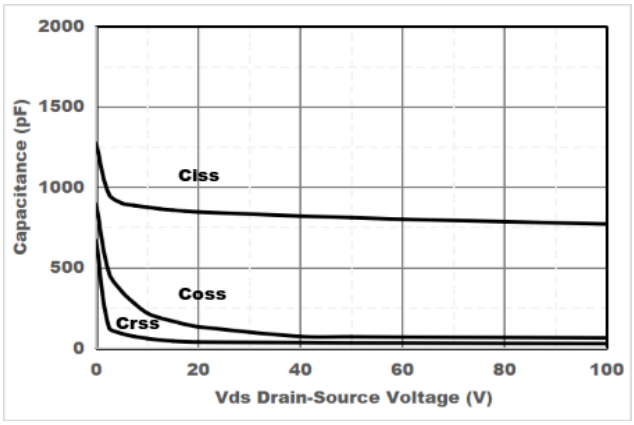


Figure3. Capacitance Characteristics

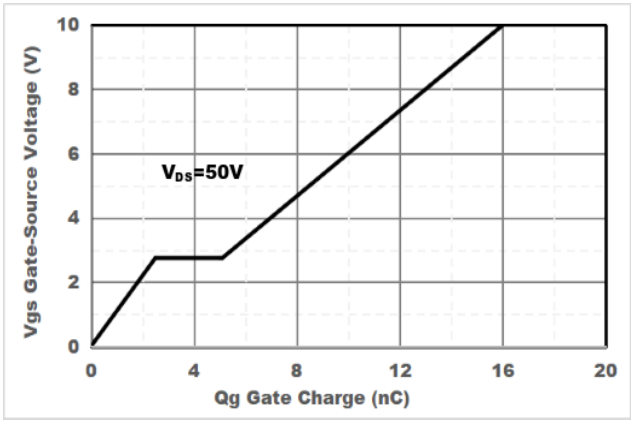


Figure4. Gate Charge

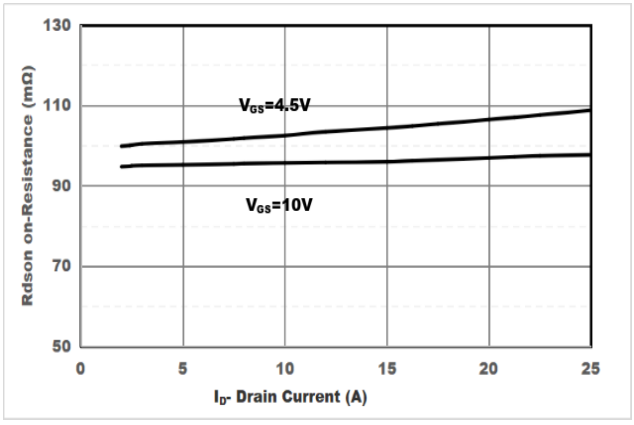


Figure5. Drain-Source on Resistance

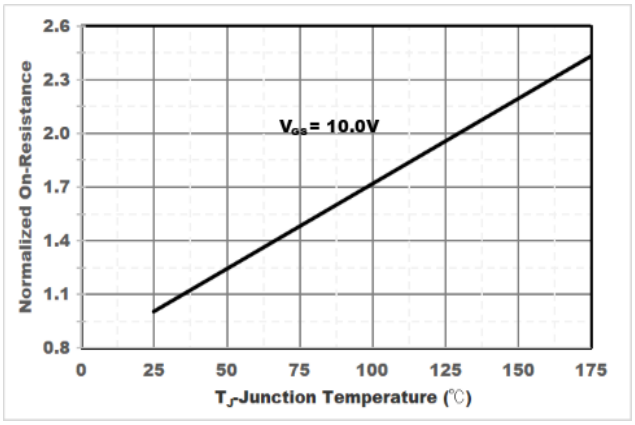
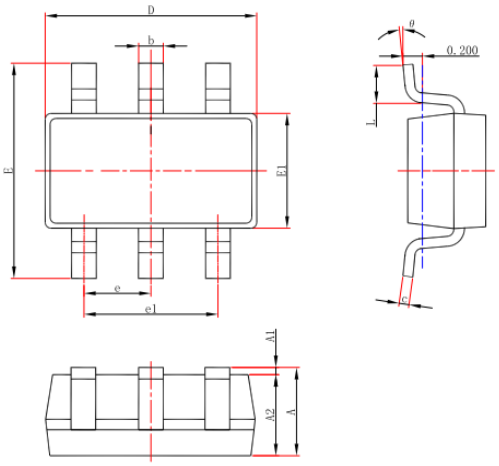


Figure6. Drain-Source on Resistance

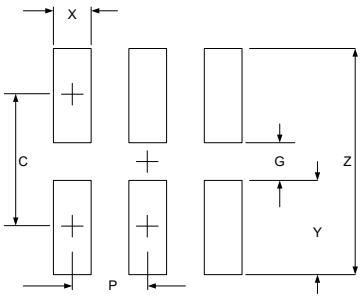
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SOT-23-6L Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.50	0.098
G	1.40	0.055
P	0.95	0.037
X	0.60	0.024
Y	1.10	0.043
Z	3.60	0.141

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